

Features

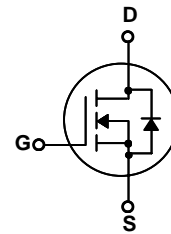
- 9 A, 500V, $R_{DS(on)} = 0.8 \Omega @ V_{GS} = 10 V$
- Low gate charge (typical 28 nC)
- Low Crss (typical 24 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

General Description

These N-Channel enhancement mode power field effect transistors are produced using Kersemi proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switched mode power supplies, active power factor correction, electronic lamp ballasts based on half bridge topology.

TO-220F

TO-220

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	KSM9N50C	KSMF9N50C	Units
V_{DSS}	Drain-Source Voltage	500		V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$) - Continuous ($T_C = 100^\circ\text{C}$)	9	9 *	A
		5.4	5.4 *	A
I_{DM}	Drain Current - Pulsed (Note 1)	36	36 *	A
V_{GSS}	Gate-Source Voltage	± 30		V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	360		mJ
I_{AR}	Avalanche Current (Note 1)	9		A
E_{AR}	Repetitive Avalanche Energy (Note 1)	13.5		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5		V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$) - Derate above 25°C	135	44	W
		1.07	0.35	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150		$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300		$^\circ\text{C}$

* Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	KSM9N50C	KSMF9N50C	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.93	2.86	$^\circ\text{C}/\text{W}$
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink Typ.	0.5	--	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	62.5	$^\circ\text{C}/\text{W}$



KSM9N50C/KSMF9N50C

Electrical Characteristics

$T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	500	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C	--	0.57	--	$\text{V}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA
		$V_{DS} = 400\text{ V}, T_C = 125^\circ\text{C}$	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 4.5\text{ A}$	--	0.65	0.8	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 40\text{ V}, I_D = 4.5\text{ A}$ (Note 4)	--	6.5	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}$	--	790	1030	pF
C_{oss}	Output Capacitance		--	130	170	pF
C_{riss}	Reverse Transfer Capacitance		--	24	30	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 250\text{ V}, I_D = 9\text{ A}, R_G = 25\ \Omega$	--	18	45	ns	
t_r	Turn-On Rise Time		--	65	140	ns	
$t_{d(off)}$	Turn-Off Delay Time		(Note 4, 5)	--	93	195	ns
t_f	Turn-Off Fall Time		(Note 4, 5)	--	64	125	ns
Q_g	Total Gate Charge	$V_{DS} = 400\text{ V}, I_D = 9\text{ A}, V_{GS} = 10\text{ V}$	--	28	35	nC	
Q_{gs}	Gate-Source Charge		(Note 4, 5)	--	4	--	nC
Q_{gd}	Gate-Drain Charge		(Note 4, 5)	--	15	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current	--	--	9	A	
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	36	A	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 9\text{ A}$	--	--	1.4	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 9\text{ A}$	--	335	--	ns
Q_{rr}	Reverse Recovery Charge	$di_F / dt = 100\text{ A}/\mu\text{s}$ (Note 4)	--	2.95	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 8\text{ mH}, I_{AS} = 9\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 9\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\ \mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

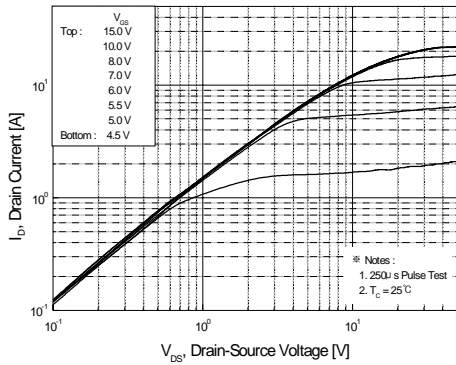


Figure 1. On-Region Characteristics

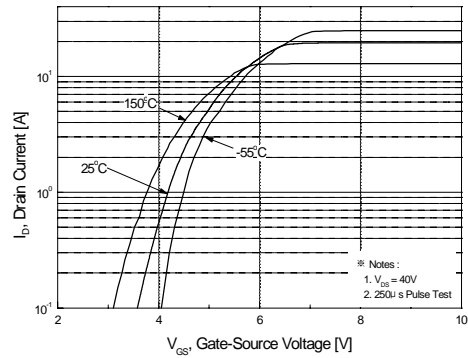


Figure 2. Transfer Characteristics

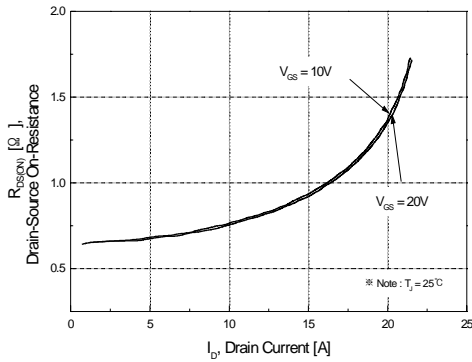


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

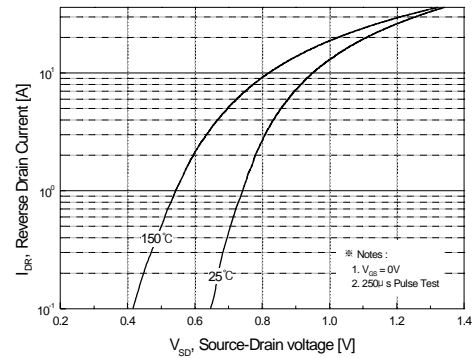


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

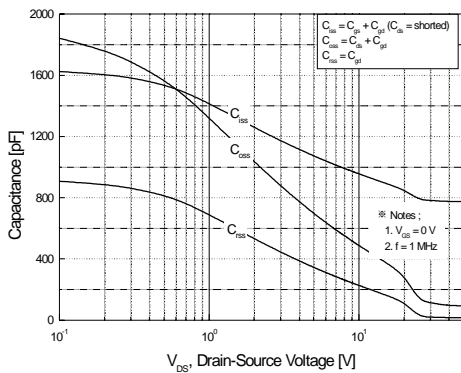


Figure 5. Capacitance Characteristics

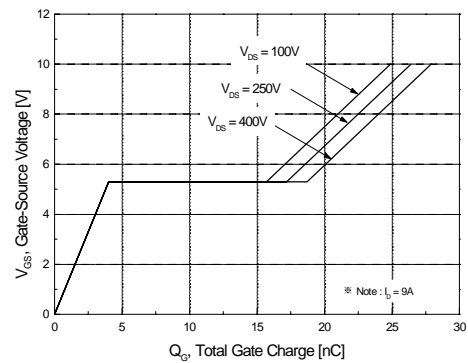
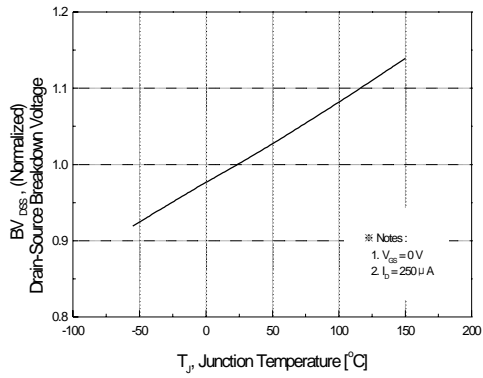
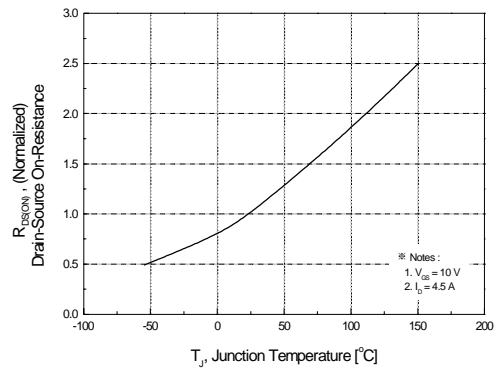
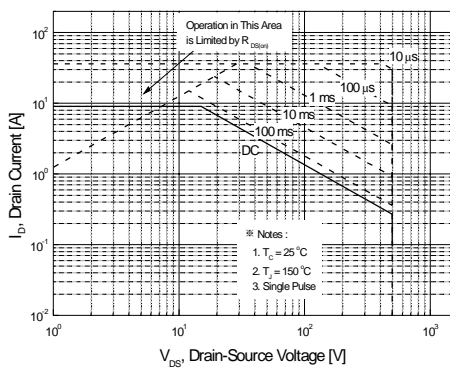
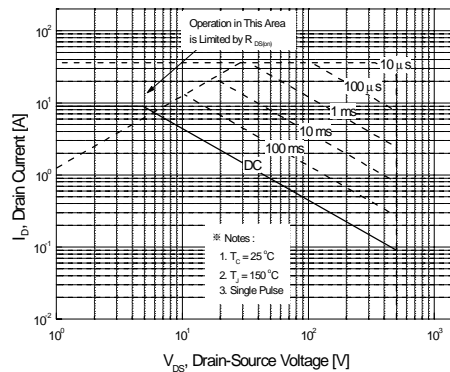
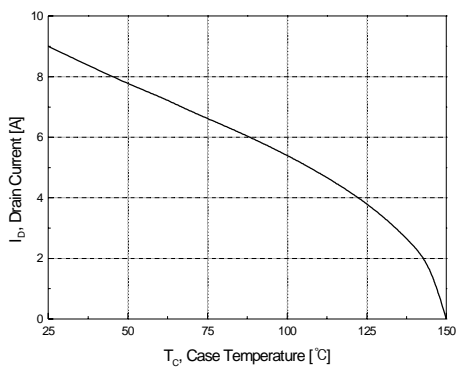
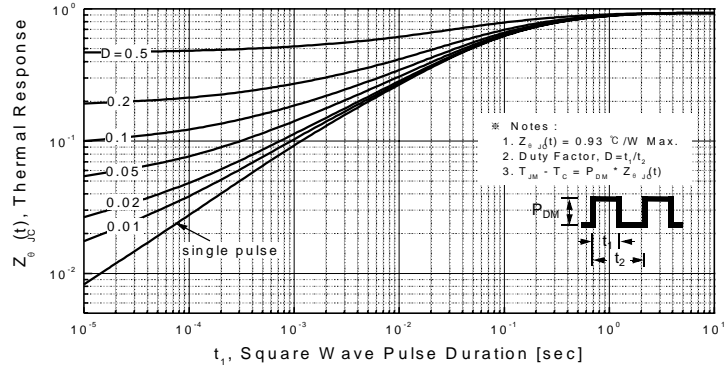
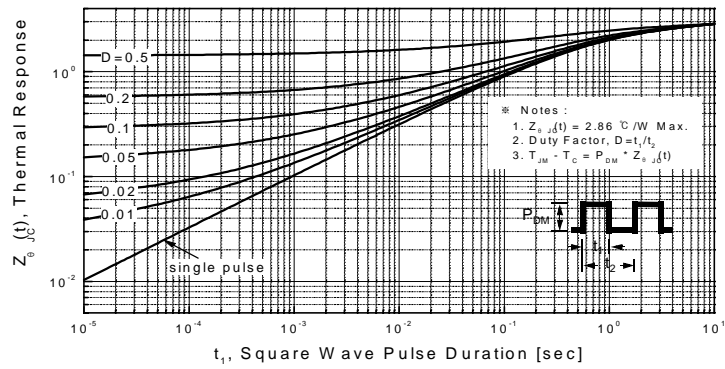
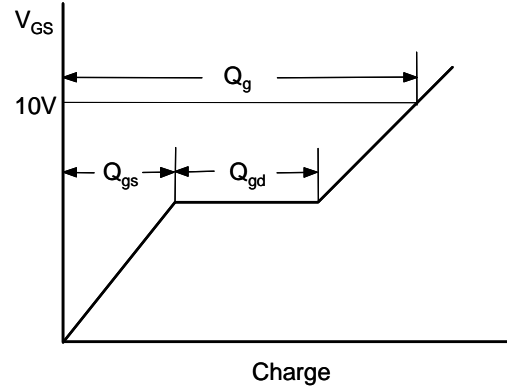
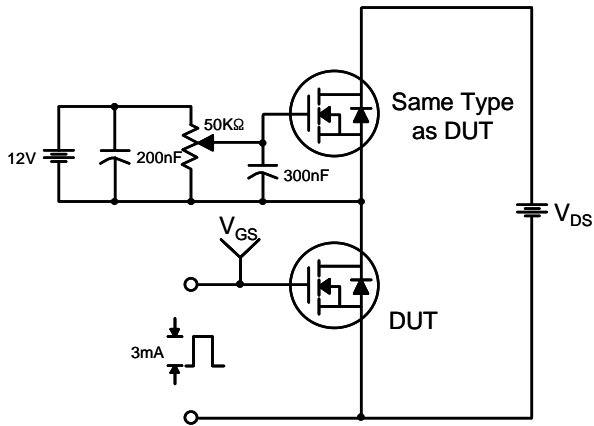
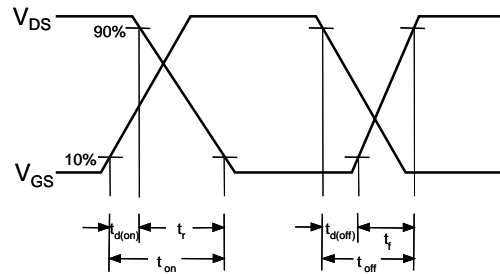
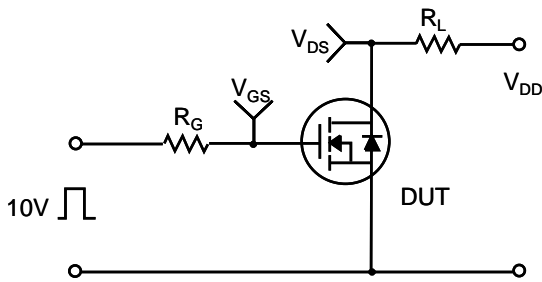
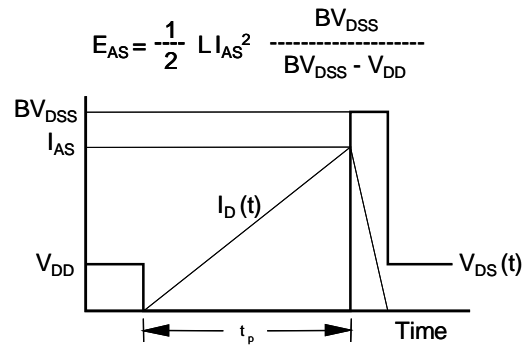
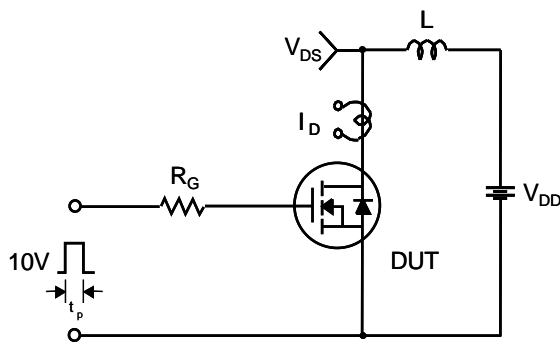
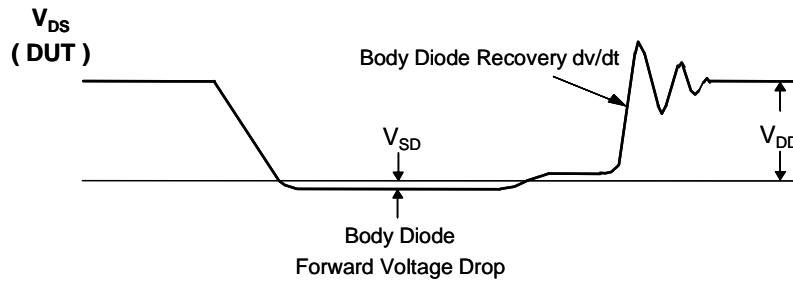
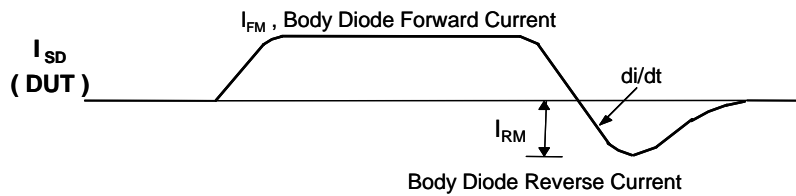
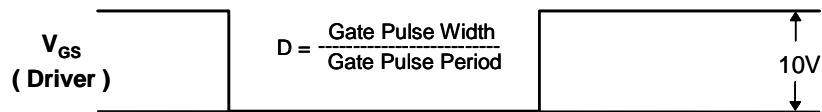
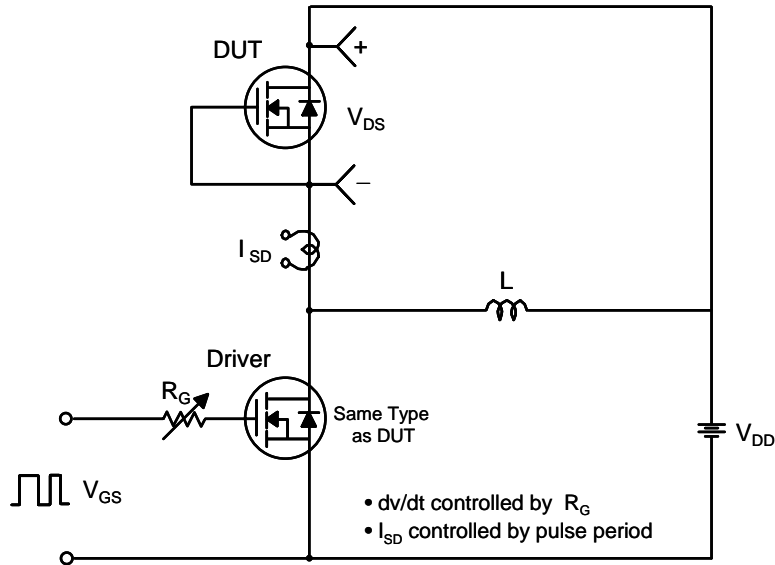


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs Temperature

Figure 8. On-Resistance Variation vs Temperature

Figure 9-1. Maximum Safe Operating Area for FQP9N50C

Figure 9-2. Maximum Safe Operating Area for FQPF9N50C

Figure 10. Maximum Drain Current vs Case Temperature

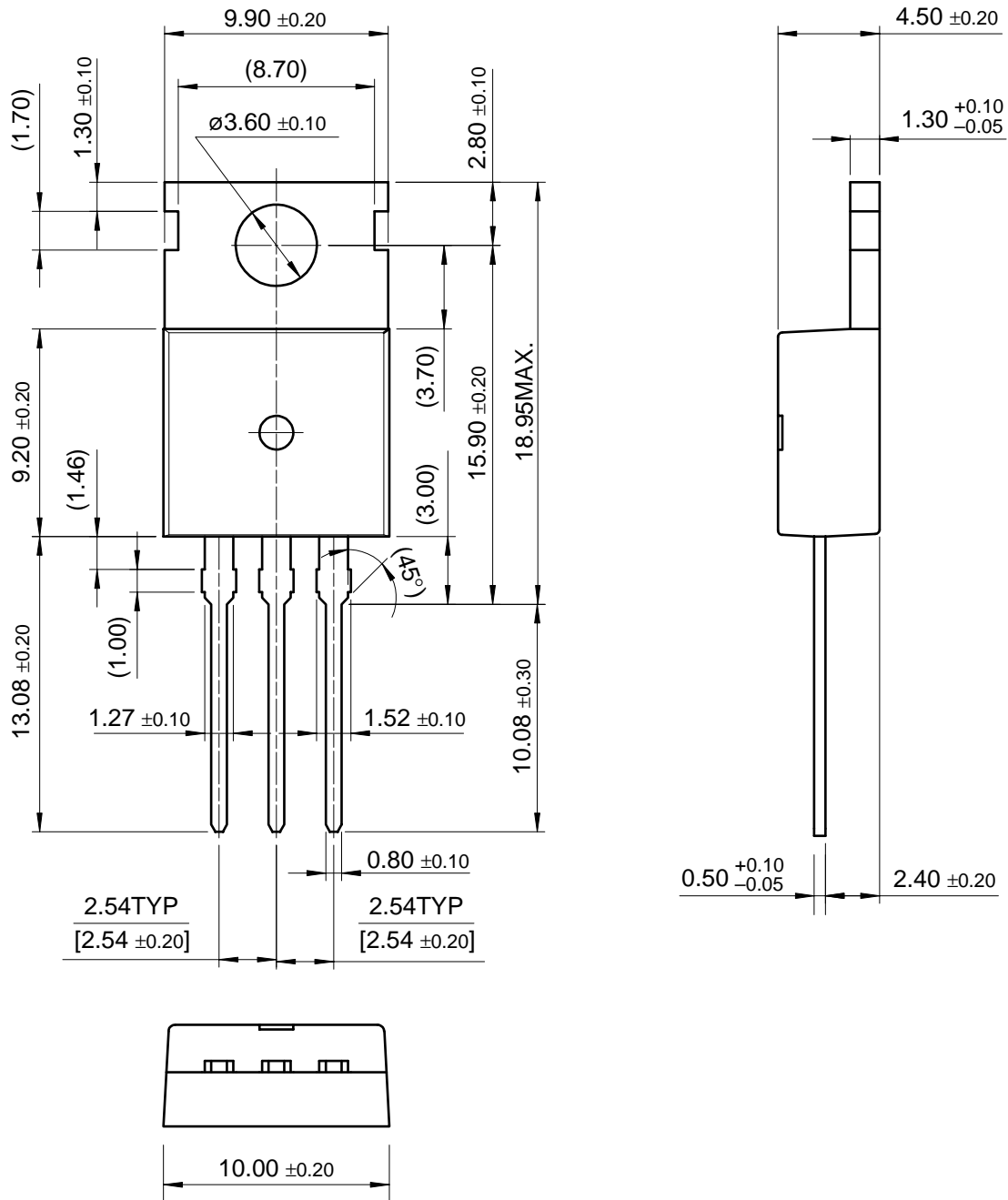
Typical Characteristics (Continued)

Figure 11-1. Transient Thermal Response Curve for FQP9N50C

Figure 11-2. Transient Thermal Response Curve for FQPF9N50C

Gate Charge Test Circuit & Waveform

Resistive Switching Test Circuit & Waveforms

Unclamped Inductive Switching Test Circuit & Waveforms


Peak Diode Recovery dv/dt Test Circuit & Waveforms


Package Dimensions

TO-220



Package Dimensions (Continued)

TO-220F
